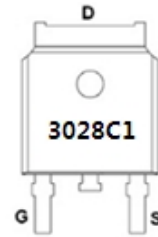
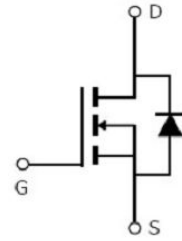


Main Product Characteristics:

V_{DSS}	30V
$R_{DS(on)}$	28mohm(typ.)
I_D	21A


TO-252

Marking and pin Assignment

Schematic diagram
Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 175°C operating temperature


Description:

It utilizes the latest trench processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications

Absolute max Rating:

Symbol	Parameter	Max.	Units
$I_D @ TC = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	21①	A
$I_D @ TC = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	15①	
I_{DM}	Pulsed Drain Current ②	84	
$P_D @ TC = 25^\circ C$	Power Dissipation ③	28	W
	Linear Derating Factor	1.2	W/°C
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy @ L=0.3mH	30	mJ
I_{AS}	Avalanche Current @ L=0.3mH	14	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

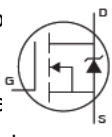
Thermal Resistance

Symbol	Characterizes	Typ.	Max.	Units
R _{θJC}	Junction-to-case ③	—	4.5	°C/W
R _{θJA}	Junction-to-ambient (t ≤ 10s) ④	—	60	°C/W

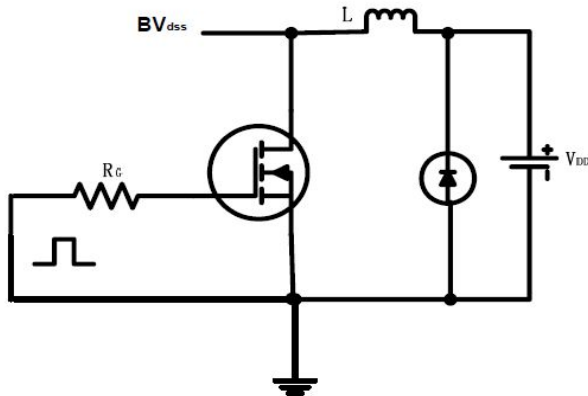
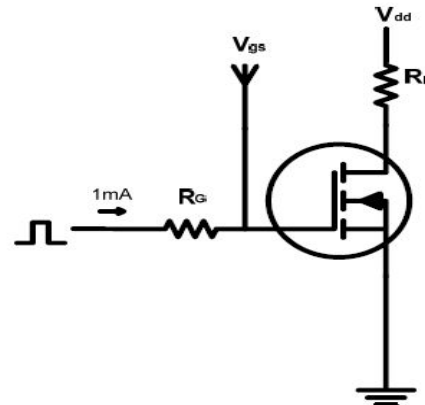
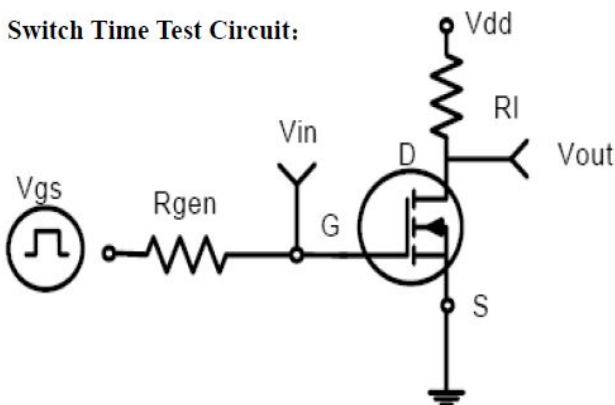
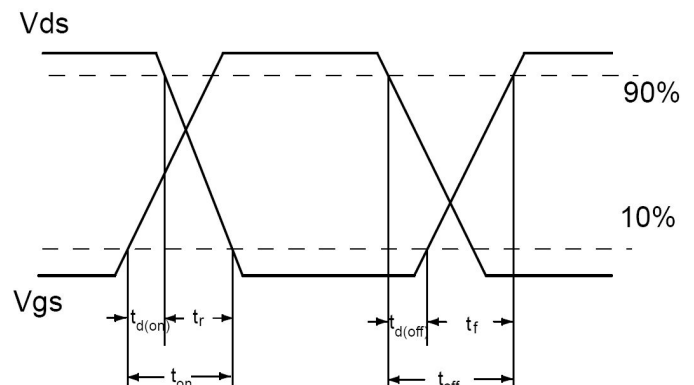
Electrical Characterizes @T_A=25°C unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source breakdown voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
R _{DS(on)}	Static Drain-to-Source on-resistance	—	28	35	mΩ	V _{GS} =10V, I _D = 7A
R _{DS(on)}	Static Drain-to-Source on-resistance	—	40	50	mΩ	V _{GS} =4.5V, I _D = 5A
V _{GS(th)}	Gate threshold voltage	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA T _J = 125°C
		—	1.11	—		
I _{DSS}	Drain-to-Source leakage current	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V T _J = 125°C
		—	—	50		
I _{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V _{GS} = 20V
		—	—	-100		V _{GS} = -20V
Q _g	Total gate charge	—	5.2	—	nC	I _D = 7.5A, V _{DS} =15V, V _{GS} = 4.5V
Q _{gs}	Gate-to-Source charge	—	2.1	—		
Q _{gd}	Gate-to-Drain("Miller") charge	—	1.2	—		
t _{d(on)}	Turn-on delay time	—	5	—	nS	V _{GS} =10V, V _{DS} =15V, R _L =15Ω, R _{GEN} =6Ω I _D =1A
t _r	Rise time	—	8	—		
t _{d(off)}	Turn-Off delay time	—	17	—		
t _f	Fall time	—	13	—		
C _{iss}	Input capacitance	—	450	—	pF	V _{GS} = 0V V _{DS} = 15V f =1MHz
C _{oss}	Output capacitance	—	110	—		
C _{rss}	Reverse transfer capacitance	—	35	—		

Source-Drain Ratings and Characteristics

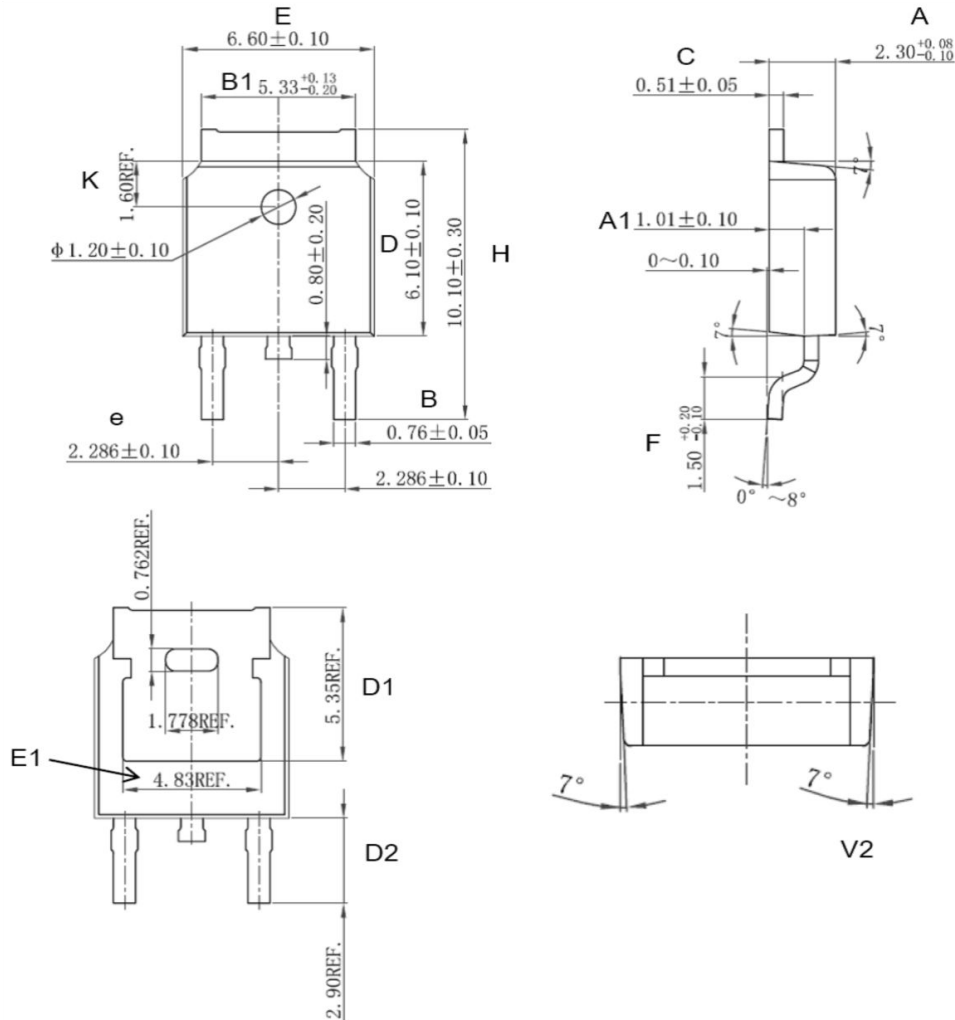
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	21①	A	MOSFET symb showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode)	—	—	84	A	
V _{SD}	Diode Forward Voltage	—	0.72	1.2	V	I _S =2.1A, V _{GS} =0V
t _{rr}	Reverse Recovery Time	—	21	—	nS	T _J = 25°C, I _F =21A, di/dt = 100A/μs
Q _{rr}	Reverse Recovery Charge	—	25.2	—	nC	

Test circuits and Waveforms

EAS test circuits:

Gate charge test circuit:

Switch Time Test Circuit:

Switch Waveforms:


Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.
- ⑤ These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)} = 175^\circ\text{C}$.

Mechanical Data:
DPAK PACKAGE OUTLINE DIMENSION


Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	2.200	2.300	2.380	0.087	0.091	0.094
A1	0.910	1.010	1.110	0.036	0.040	0.044
B	0.710	0.760	0.810	0.028	0.030	0.032
B1	5.130	5.330	5.460	0.202	0.210	0.215
C	0.460	0.510	0.560	0.018	0.020	0.022
D	6.000	6.100	6.200	0.236	0.240	0.244
D1	5.350 (REF)			0.211 (REF)		
D2	2.900 (REF)			0.114 (REF)		
E	6.500	6.600	6.700	0.256	0.260	0.264
E1	4.83 (REF)			0.190 (REF)		
e	2.186	2.286	2.386	0.086	0.090	0.094
H	9.800	10.100	10.400	0.386	0.398	0.409
F	1.400	1.500	1.700	0.055	0.059	0.067
K	1.600 (REF)			0.063 (REF)		
V2	8° (REF)			8° (REF)		

Ordering and Marking Information
Device Marking: 3028C1

Package (Available)
DPAK (TO-252)
Operating Temperature Range
C : -55 to 150 °C

Devices per Unit
Option1:

Package Type	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO-252	2500	2	5000	7	35000

Option2:

Package Type	Units/Tape	Tapes/Inner Box	Units/Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO-252	2500	1	2500	10	25000

Reliability Test Program

Test Item	Conditions	Duration	Sample Size
High Temperature Reverse Bias(HTRB)	T _j =150°C @ 80% of Max V _{DSS} /V _{CES} /VR	168 hours 500 hours 1000 hours	3 lots x 77 devices
High Temperature Gate Bias(HTGB)	T _j =150°C @ 100% of Max V _{GSS}	168 hours 500 hours 1000 hours	3 lots x 77 devices

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